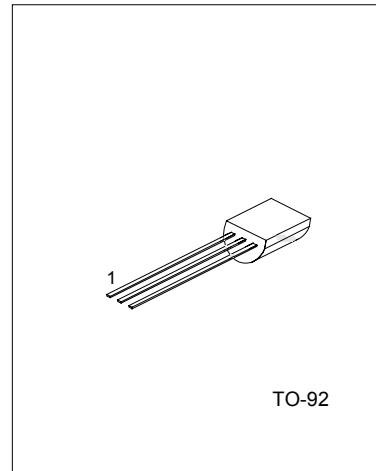


# UTC2SC1815 NPN EPITAXIAL SILICON TRANSISTOR

AUDIO FREQUENCY AMPLIFIER  
HIGH FREQUENCY OSC NPN  
TRANSISTOR

## FEATURES

- \*Collector-Emitter voltage:  
 $BV_{CEO}=50V$
- \*Collector current up to 150mA
- \* High hFE linearity
- \*complimentary to 2SA1015



TO-92

1:EMITTER 2:COLLECTOR 3. BASE

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^{\circ}C$ ,unless otherwise specified )

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	$V_{CBO}$	60	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector dissipation( $T_a=25^{\circ}C$ )	$P_c$	400	mW
Collector current	$I_c$	150	mA
Base current	$I_B$	50	mA
Junction Temperature	$T_j$	125	$^{\circ}C$
Storage Temperature	$T_{STG}$	-55 ~ +150	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS( $T_a=25^{\circ}C$ ,unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	$I_{CBO}$	$V_{CB}=60V, I_E=0$			100	nA
Emitter cut-off current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			100	nA
DC current gain(note)	$h_{FE1}$ $h_{FE2}$	$V_{CE}=6V, I_C=2mA$ $V_{CE}=6V, I_C=150mA$	70 25		700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100mA, I_B=10mA$		0.1	0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100mA, I_B=10mA$			1.0	V
Current gain bandwidth product	$f_T$	$V_{CE}=10V, I_C=50mA$	80			MHz
Output capacitance	$C_{OB}$	$V_{CB}=10V, I_E=0, f=1MHz$		2.0	3.0	pF
Noise Figure	NF	$I_C=-0.1mA, V_{CE}=6V$ $R_G=10k\Omega, f=100Hz$		1.0	1.0	dB

# UTC2SC1815 NPN EPITAXIAL SILICON TRANSISTOR

---

## CLASSIFICATION OF hFE1

RANK	Y	G	L
RANGE	120-240	200-400	350-700

## TYPICAL CHARACTERISTIC CURVES

Fig.1 Static characteristics

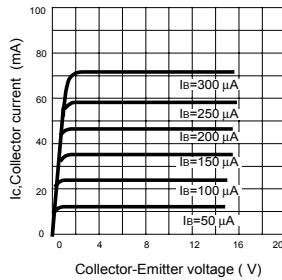


Fig.2 DC current Gain

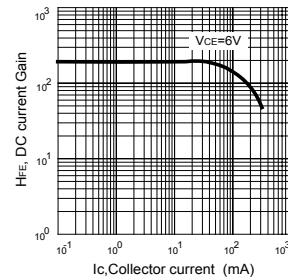


Fig.3 Base-Emitter on Voltage

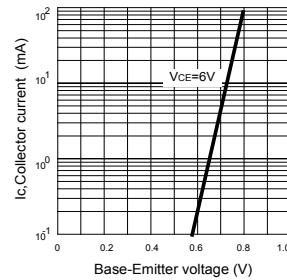


Fig.4 Saturation voltage

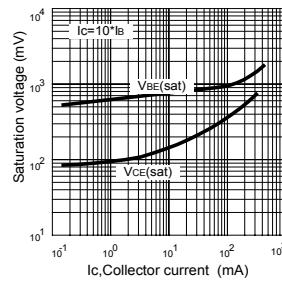


Fig.5 Current gain-bandwidth product

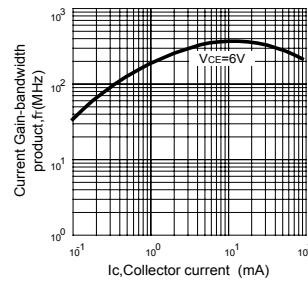


Fig.6 Collector output Capacitance

